

Electron-doped phosphorene: A potential monolayer superconductor

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Abstract – We predict by first-principles calculations that the electron-doped phosphorene is a potential BCS-like superconductor. The stretching modes at the Brillouin-zone center are remarkably softened by the electron-doping, which results in the strong electron-phonon coupling. The superconductivity can be introduced by a doped electron density (n_{2D}) above $1.3 \times 10^{14} \text{ cm}^{-2}$, and may exist over the liquid helium temperature when $n_{2D} > 2.6 \times 10^{14} \text{ cm}^{-2}$. The superconductivity can be significantly tuned and enhanced by applying tensile strain. The maximum critical temperature of electron doped phosphorene is predicted to be higher than 10 K. The superconductivity of phosphorene will significantly broaden the applications of this novel material.

The two-dimensional (2D) monolayer superconductor bears consequences for both applications and fundamental science. It can be used as the component of nanoscale superconducting devices, such as nano superconducting quantum interference devices and nano superconducting transistors [1–5], with the goal of achieving single-spin sensitivity for measuring and controlling. Moreover, the high- T_c superconductors with the quasi-2D layered structures, such as MgB₂ [6], cuprate superconductors [7,8], and iron-based superconductors [9], can be seen as the assembly of multiple monolayers. Geim *et al.* [10] proposed to construct the high- T_c -superconductor-like Van der Waals heterostructures using the monolayer superconductors, which may be helpful for the exploration of new high- T_c superconductors. A graphene-like monolayer superconductor seems to be the natural choice of such applications. It is suggested that the carrier-doped graphene [11–13] and graphane [14] may exhibit superconductivity with notable T_c . However, the experimental evidences are still lacking. Using the liquid-gate method, one can introduce the superconductivity into the few-layer semiconductor MoS₂ [15], which may be driven by the electron-phonon coupling

[16]. But the thickness of such material is still far from one layer. More monolayer superconductor candidates still need to be found.

Here we show a potential monolayer superconductor: electron-doped phosphorene. Based on the density functional theory (DFT) calculations, we found the electron-doping can make the stretching modes at zone center significantly softened, leading to a strong electron-phonon coupling. The superconductivity starts showing up when the carrier density (n_{2D}) is $1.3 \times 10^{14} \text{ cm}^{-2}$. When $n_{2D} > 2.6 \times 10^{14} \text{ cm}^{-2}$, the T_c exceeds the liquid helium temperature. Moreover, the application of tensile strain can significantly tune and enhance the superconductivity. The maximum T_c is predicted to be higher than 10 K. Our prediction can be readily verified by the liquid-gate method [15,17–19], or the adsorption of the alkali/alkaline-earth metal atoms.

Figure 1 shows the structures of bulk black phosphorus (black-P) and monolayer black-P (which is called phosphorene). Phosphorene can be obtained by exfoliating the black-P [20,21], the most stable allotropic form of phosphorus and the only layered structure of an elemental solid besides graphitic carbon [22]. The phosphorus atoms are covalently bonded, forming a special puckered 2D structure [23–25]. Both bulk black-P and phosphorene

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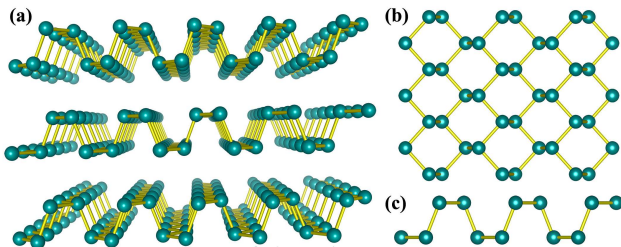


Fig. 1: (a) Structure of bulk black phosphorus. (b) and (c) are the top and side views of the structure of phosphorene, respectively.

are direct-gap semiconductors, in which the gap increases from 0.3 eV in bulk black-P to 2 eV in phosphorene with decreasing the number of layers [26–32]. Recent theoretical and experimental works showed that phosphorene is a good candidate to realize the novel optoelectronic, electronic, thermoelectric, and nano-mechanical devices because of such band properties [20, 21, 33–37]. If the superconductivity can be introduced, the applications of phosphorene will be significantly broadened.

In this letter, we performed the DFT calculations to investigate the potential superconductivity in electron-doped phosphorene. Calculations were carried out using the QUANTUM-ESPRESSO package [38]. The ultrasoft pseudopotential within the generalized gradient approximation (GGA) according to the Perdew-Burke-Ernzerhof [39] was used. The energy cutoff for the plane-wave basis set was 40 Ry. The Brillouin zone was sampled with a $32 \times 24 \times 1$ mesh of k points. The Vanderbilt-Marzari Fermi smearing method with a smearing parameter of $\sigma = 0.02$ Ry was used for the calculations of the total energy and electron charge density. Phonon spectra and electron-phonon coupling constants were calculated using density-functional perturbation theory [40] with an $8 \times 8 \times 1$ mesh of q points. The double Fermi-surface averages of electron-phonon matrix elements were calculated using the tetrahedron method on grids of $160 \times 120 \times 1$ k points. To simulate the monolayer, a vacuum layer more than 10 Å was introduced.¹ Electron-doping was simulated by adding electrons into the system, together with a compensating uniform positive background [16]. For each doping concentration, we relaxed the atomic positions with the fixed in-plane lattice constants of the optimized lattice structure of the undoped phosphorene.

Figure 2 shows the conduction bands and the corresponding Fermi sheets of three typical doping concentrations. The effect of doping obviously enlarges the Fermi surface. For the low doping concentrations, electrons oc-

¹ For the low doping concentration of $x = 0.1$ electrons/cell, the smaller $\sigma = 0.005$ Ry and the denser $64 \times 48 \times 1$ mesh of k points were used. For the vacuum layer, we tested different values of the thickness. It turns out a vacuum layer more than 10 Å can lead to the converged lattice parameters ($a = 3.32$ Å and $b = 4.64$ Å) and band structure (the band gap is ~ 0.9 eV) in good agreement with the previous PBE calculation [34].

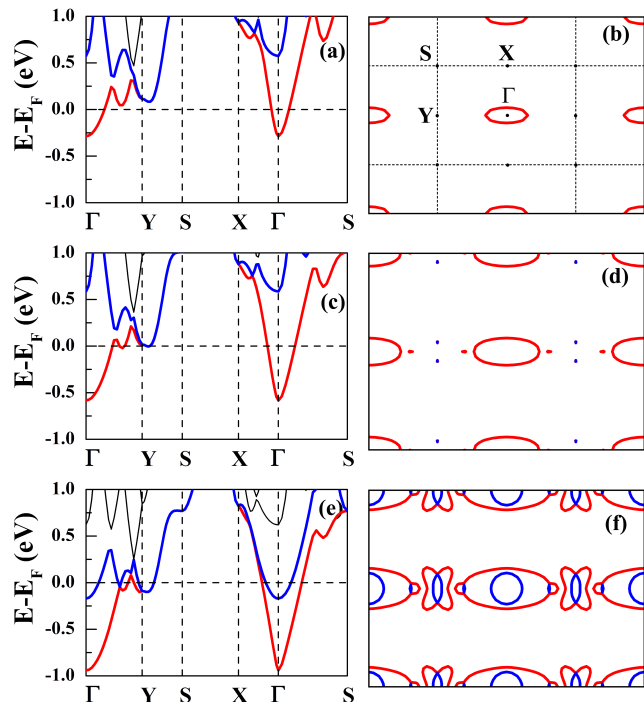


Fig. 2: Conduction bands and Fermi surface of phosphorene. (a), (c), and (e) are the band structures with respect to the doping concentrations of $x = 0.1, 0.3,$ and 0.7 electrons/cell, respectively. (b), (d), and (f) show the corresponding Fermi sheets. The red and blue lines denote the Fermi sheets from the lowest and second-lowest conduction band, respectively. The high symmetry points are denoted in (b).

cupy the states near the conduction band minimum at Γ point, forming an oval Fermi sheet around the zone center, as shown in figs. 2 (a) and (b). When the doping concentration is up to $x = 0.3$ electrons/cell, the second-lowest conduction band starts crossing the Fermi level (E_F) at the place near Y point, and new sheets start to show up, as shown in figs. 2 (c) and (d). These sheets expand with increasing the doping concentration. When the doping concentration is above $x = 0.7$ electrons/cell, the Γ valley of the second lowest conduction band is occupied. The valley becomes the energy minimum of such band, and forms a circle-like Fermi sheet around the zone center (figs. 2 (e) and (f)). Such relative shift in energy of the conduction band valleys with doping was also found in the electron-doped monolayer MoS_2 [16].

The calculated phonon dispersions of the pristine and electron-doped phosphorene are presented in fig. 3. For the pristine phosphorene, our calculation is in good agreement with the previous result reported by Zhu and Tománek [22]. Compared with the zone center modes of phosphorene recently measured and bulk black phosphorus previously reported [20, 41–44], our calculated zone center modes seem to have slightly smaller frequencies. It might be due to the overestimation of lattice constant for PBE [34]. However, our calculation is still enough to dis-

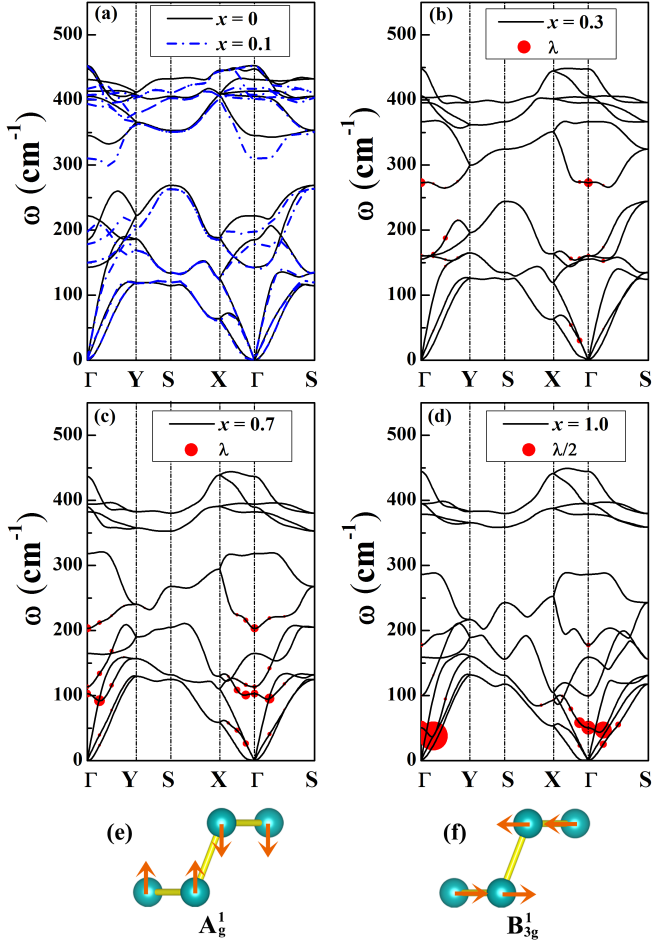


Fig. 3: Phonon dispersions of phosphorene with some typical doping concentrations: (a) $x = 0$ (pristine sample, black solid lines) and $x = 0.1$ (blue dashed lines), (b) $x = 0.3$, (c) $x = 0.7$, and (d) $x = 1.0$ electron/cell. The phonon dispersions in (b), (c), and (d) are decorated with symbols, proportional to the partial electron-phonon coupling strength $\lambda_{\nu\mathbf{q}}$. The A_g^1 (e) and B_{3g}^1 (f) stretching modes in zone center are showed in the bottom.

Discuss the variation trends of the properties upon doping. In fig. 3, one can notice that the highest four optical branches are slightly softened while other five optical branches are softened significantly upon doping. A remarkable softening can be found in the high frequency optical zone center A_g^1 mode associated with the outplane stretching (fig. 3 (e)). The region of the reciprocal space where the softening is observed matches the diameter $2k_F$ of the Fermi sheets around Γ , which is a typical signature of the Kohn effect [45]. Such softening generally exists in some superconductors such as MgB_2 [46, 47], hole-doped diamond [48, 49], hole-doped graphane [14], etc.. When the doping concentration is above $x = 0.7$ electrons/cell, A_g^1 mode is further softened. This is due to a new Kohn anomaly caused by the new Γ centered circular Fermi sheets from the second-lowest conduction band (see figs. 2 (e) and (f)). Another prominent softening happens in the low fre-

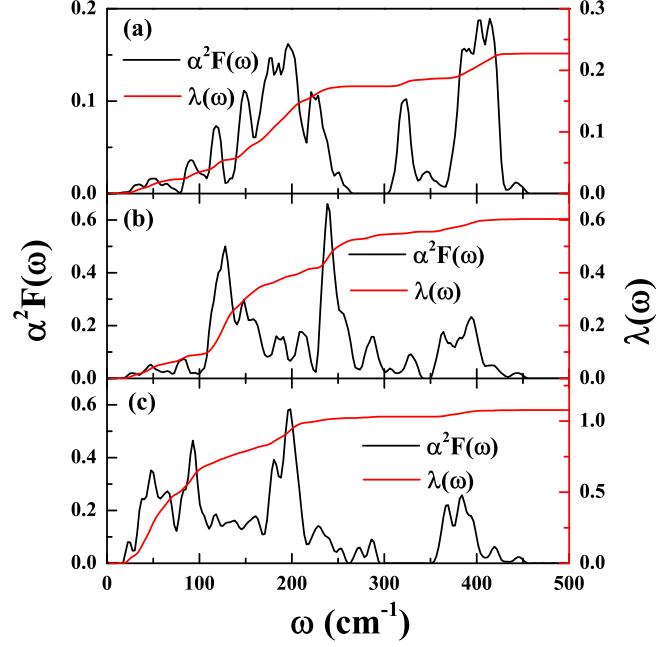


Fig. 4: (a) Eliashberg function (left) and the integrated electron-phonon coupling strength (right) for the electron-doped phosphorene with $x = 0.1$ (a), 0.5 (b), and 1.0 (c) electron/cell.

quency optical mode B_{3g}^1 at zone center, which is related to the inplane stretching (fig. 3 (f)). For the pristine phosphorene, the B_{3g}^1 mode has the highest energy among the low frequency optical modes at zone center. With the electron-doping, the B_{3g}^1 mode significantly softens, and gradually becomes frequency minimum of the optical modes at Γ . Besides the two remarkable softenings at the zone center, some other anomalies, such as the anomaly at $\mathbf{q} \approx \frac{1}{4}\Gamma Y$ (figs. 3 (c) and (d)), have been found in the low frequency optical branches. These anomalies start to show up for $x = 0.3$ electrons/cell, when the new Fermi sheets are introduced into the system. It indicates such anomalies might be due to the nesting between the Fermi sheets. When $x \geq 1.2$ electrons/cell, frequencies of B_{3g}^1 and its adjacent modes become negative, indicating the appearance of the lattice instability induced by doping. Such instability suggests the electron-doping limit of phosphorene should be smaller than 1.2 electrons/cell.

Figure 4 plots the Eliashberg spectral function:

$$\alpha^2 F(\omega) = \frac{1}{N(E_F)} \sum_{\mathbf{k}, \mathbf{q}, \nu, n, m} \delta(\epsilon_{\mathbf{k}}^n) \delta(\epsilon_{\mathbf{k}+\mathbf{q}}^m) |g_{\mathbf{k}, \mathbf{k}+\mathbf{q}}^{\nu, n, m}|^2 \delta(\omega - \omega_{\mathbf{q}}^{\nu}), \quad (1)$$

where $N(E_F)$ is the density of states at E_F , $\omega_{\mathbf{q}}^{\nu}$ is phonon frequency, $\epsilon_{\mathbf{k}}^n$ is electronic energy, and $g_{\mathbf{k}, \mathbf{k}+\mathbf{q}}^{\nu, n, m}$ is electron-phonon coupling matrix element. The total electron-phonon coupling strength is then

$$\lambda = 2 \int_0^{\infty} \frac{\alpha^2 F(\omega)}{\omega} d\omega = \sum_{\nu \mathbf{q}} \lambda_{\nu \mathbf{q}}. \quad (2)$$

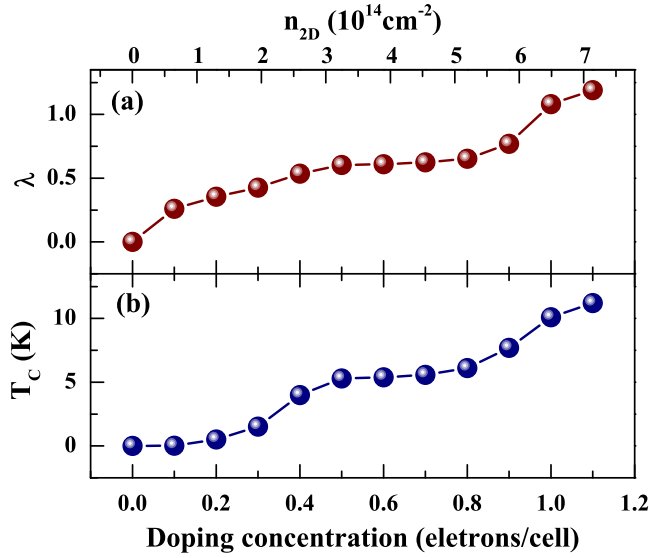


Fig. 5: (a) Total electron phonon coupling strength λ and (b) predicted T_c with different doping concentrations. The carrier density corresponding to the doping concentration is shown at the top axis.

$\lambda_{\nu\mathbf{q}}$ are visualized as red circles in fig. 3. Acoustic modes near Γ contribute a small peak to the $\alpha^2 F(\omega)$ (fig. 4 (a) and (b)). But the predominant contribution is from the softened optical modes. The large contribution of electron-phonon coupling from the A_g^1 mode leads to a sharp peak in $\alpha^2 F(\omega)$ at high frequency (fig. 4)). Another remarkable contribution is from the softening of B_{3g}^1 mode. Moreover, one can notice that when new Fermi sheets are introduced, the $\lambda_{\mathbf{q}}$ at some \mathbf{q} -vector, such as $\mathbf{q} \approx \frac{1}{4}\Gamma Y$ (see figs. 3 (c) and (d)), is largely enhanced. It indicates that the intersheet nesting plays an important role in the electron-phonon coupling as well, similar to the cases in hole doped CuAlO_2 [50, 51] and electron doped monolayer MoS_2 [16]. For the high doping concentration, because of the very low ω in the denominator of eq. (2), the contributions of B_{3g}^1 and its adjacent modes to the electron-phonon coupling become predominant.

We estimated the T_c based on the Allen-Dynes formula [52]

$$T_c = \frac{\omega_{log}}{1.2} \exp\left(-\frac{1.04(1+\lambda)}{\lambda - \mu^* - 0.62\lambda\mu^*}\right), \quad (3)$$

where the Coulomb pseudopotential μ^* is set to a typical value of $\mu^* = 0.1$. The logarithmically averaged characteristic phonon frequency ω_{log} is defined as

$$\omega_{log} = \exp\left(\frac{2}{\lambda} \int \frac{d\omega}{\omega} \alpha^2 F(\omega) \log \omega\right). \quad (4)$$

The calculated total electron-phonon coupling strength λ and T_c of the electron-doped phosphorene with different doping concentrations are presented in figs. 5 (a) and (b), respectively. For the low doping concentration, the electron-phonon coupling is weak. It gradually increases

with increasing doping concentration. When the doping concentration is up to $x = 0.2$ electrons/cell ($1.3 \times 10^{14} \text{ cm}^{-2}$), the superconductivity starts showing up. The calculated $\lambda = 0.36$ leads to the superconductivity with $T_c \sim 0.5$ K, which already can be detected in routine measurements. When $x > 0.4$ electron/cell ($n_{2D} > 2.6 \times 10^{14} \text{ cm}^{-2}$), the value of λ is above 0.54, generating the superconductivity with T_c above the liquid helium temperature of 4.2 K. The maximum T_c is predicted to be 11.2 K when $x = 1.1$ electrons/cell. Such value can be comparable to the maximum T_c of high pressure phase of phosphorus [53–55], clearly indicating that the electron-doped phosphorene may be another superconducting phase of phosphorus.

The electron doping can be processed using the liquid-gate method, which is considered as a clean route to dope carrier without introducing randomly distributed charged impurities which strongly scatter charge carriers. [15, 17–19, 56, 57] Applying the method to a film with the thickness of several unit cells, an extremely high density of electrons can be accumulated in a very thin depth below the sample surface [15]. Due to the very large interlayer distance of black phosphorus ($\sim 5 \text{ \AA}$), it is reasonable to assume the electrons doped by liquid-gate method will be mainly confined in the top monolayer [15]. Therefore, our calculation can be seen as a direct simulation of the liquid-gate doping. The maximum n_{2D} of the method reported is $8 \times 10^{14} \text{ cm}^{-2}$ [56, 57]. Since the superconductivity we predicted is detectable when n_{2D} above a low carrier density of $1.3 \times 10^{14} \text{ cm}^{-2}$, our prediction can be readily verified using such method.

In order to obtain a free standing superconductor, the chemical doping is necessary. Intercalation is an usual method to dope electrons into layered materials. However, for the black phosphorus system, to the best of our knowledge, there are no homogeneous and stable donor intercalated compounds yet [58]. Although the donor-type atoms or molecules can hardly be intercalated inside the interlayers, it is suggested that those can be adsorbed at the surface [29], which implies the chemical doping by adsorption for monolayer will be much easier and more efficient than that for bulk. Alkali atom Cs might be a promising donor-type atom for the adsorption [58]. The bands of the adsorbed atoms in phosphorene may occur at the E_F and have multiple beneficial effects on λ [11, 59], which may enhance the superconductivity.

Since the strain is proven to be a key method to control the properties of nanoscale material [13, 37], we also investigated the strain effects in the electron doped phosphorene. We found that the strain can significantly tune and enhance the superconductivity. As an example, fig. 6 shows the influence of tensile strain along armchair direction on electron doped phosphorene with doping concentration of $x = 0.4$ electrons/cell. The B_{3g}^1 mode is largely softened by strain, which strongly enhances the electron phonon coupling and raises T_c . When a strain about 8% is applied, the maximum $T_c = 12.2$ K can be obtained.

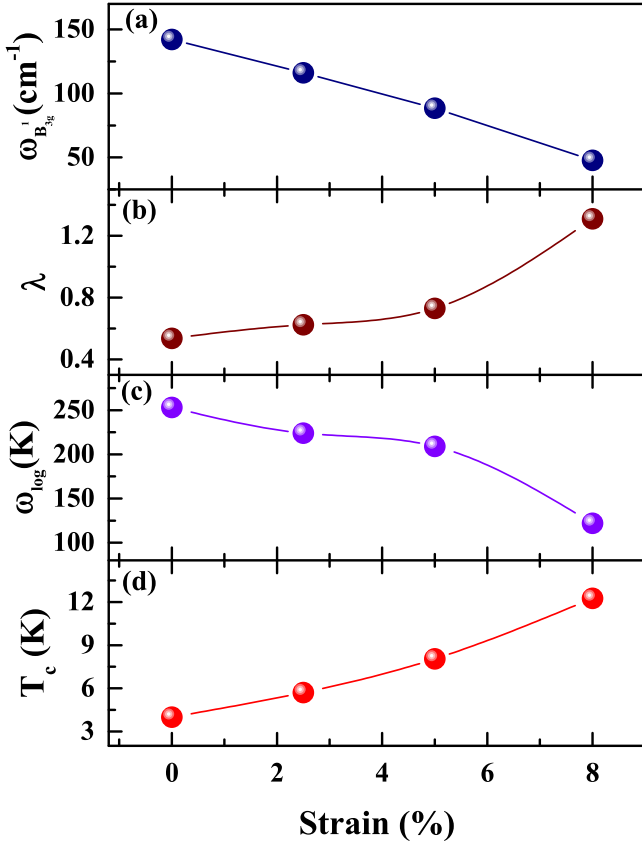


Fig. 6: The effect of strain along armchair direction for the 0.4 electron doped phosphorene: The variation of (a) frequency of B_{3g}^1 , (b) total electron phonon coupling strength λ , (c) the logarithmically averaged characteristic phonon frequency ω_{log} and (d) predicted T_c under different strains along armchair direction.

One can notice the strain strongly suppressed ω_{log} , which limits the increase of T_c . Moreover, a very large strain can make the B_{3g}^1 mode unstable. Therefore, a very high T_c cannot be achieved in electron doped phosphorene. However, the application of strain is still an useful method to achieve superconductivity with T_c over 10 K for low doping concentration.

In conclusion, we have carried out the first-principles study of phosphorene and found that the phonon mediated superconductivity can be introduced by a doped electron density above $1.3 \times 10^{14} \text{ cm}^{-2}$. When $n_{2D} > 2.6 \times 10^{14} \text{ cm}^{-2}$, the T_c exceeds the liquid helium temperature. Moreover, the superconductivity can be significantly tuned and enhanced by strain. A maximum T_c over 10 K can be achieved. The electron-phonon coupling is majorly contributed by the softening of the outplane stretching mode A_g^1 and the inplane stretching mode B_{3g}^1 . Our prediction indicates that phosphorene can be a good platform to realize the nanoscale superconducting devices. Moreover, it can be the “atomic-scale Lego” to construct the van der waals heterostructure for the attempt of searching for the high T_c superconductivity.

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